

In the Claims:

~~Claim 2 (amended).~~ The semiconductor configuration according to claim 1, wherein:

said first connection zone and said second connection zone define the lateral direction as extending from said first connection zone to said second connection zone;

~~at least one of said first and second connection zones has a first dimension in the vertical direction and a second dimension in the lateral direction; and~~

~~said second dimension is smaller than said first dimension.~~

~~Claim 15 (amended).~~ The semiconductor configuration according to claim ~~1~~, wherein said first dopant concentration is higher than 10^{18} cm^{-3} .

~~Claim 16 (amended).~~ The semiconductor configuration according to claim ~~2~~, wherein said second dopant concentration is substantially $5 \times 10^{15} \text{ cm}^{-3}$.

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